



FIG. 1A

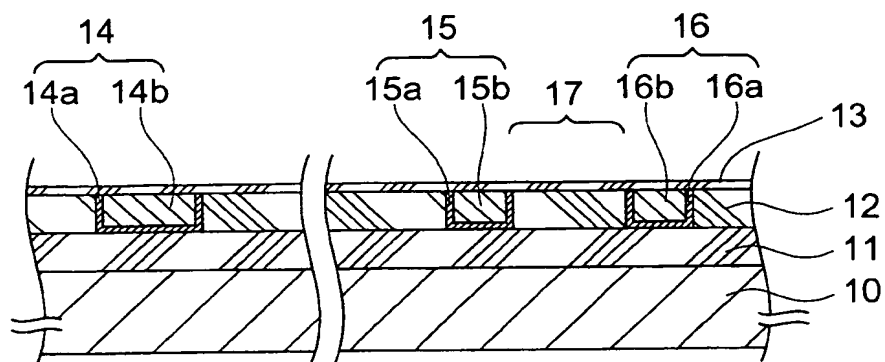


FIG. 1B

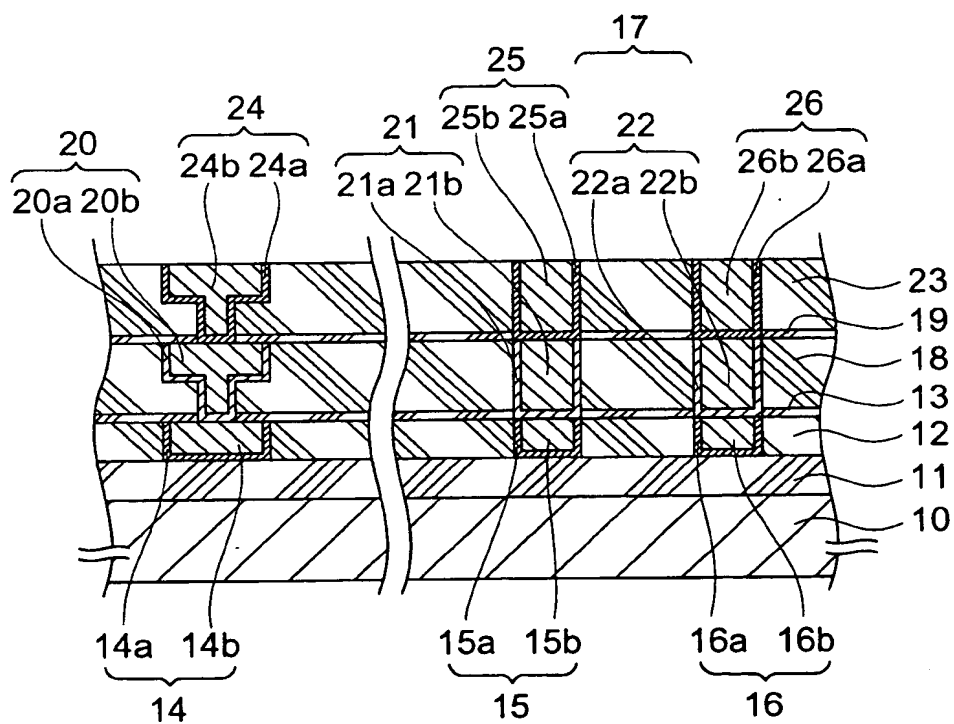


FIG. 2A

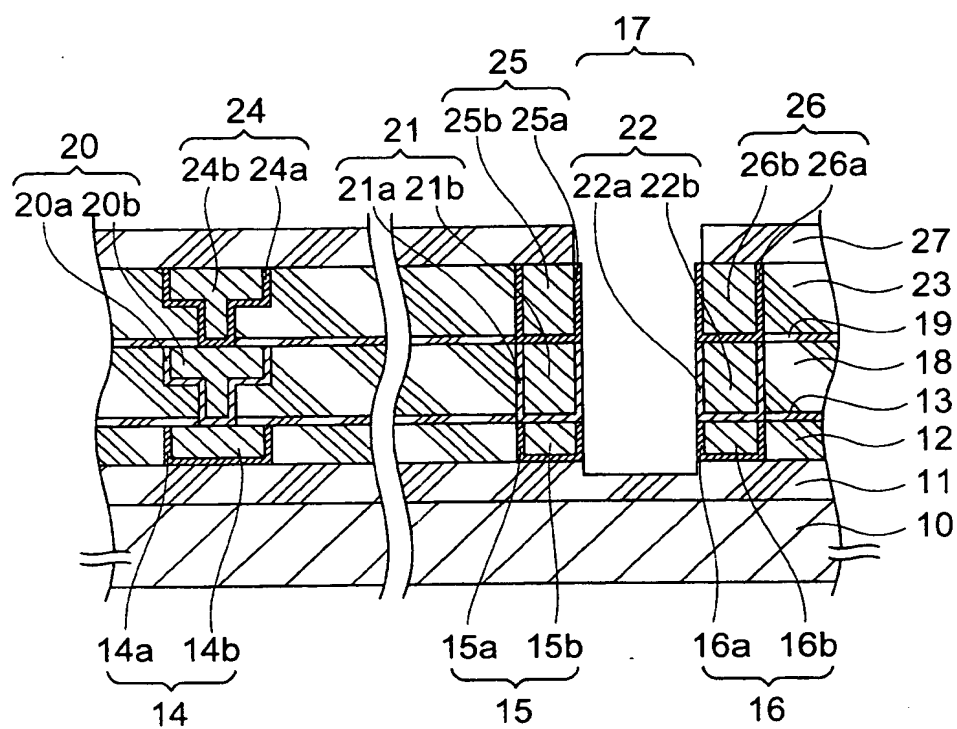


FIG. 2B

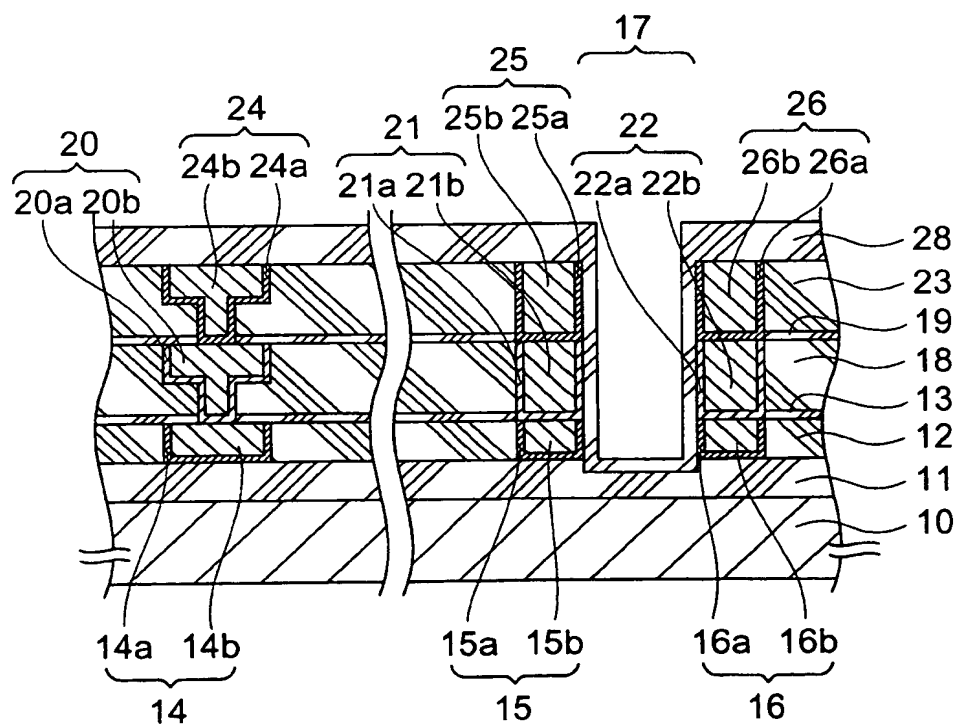


FIG. 3A

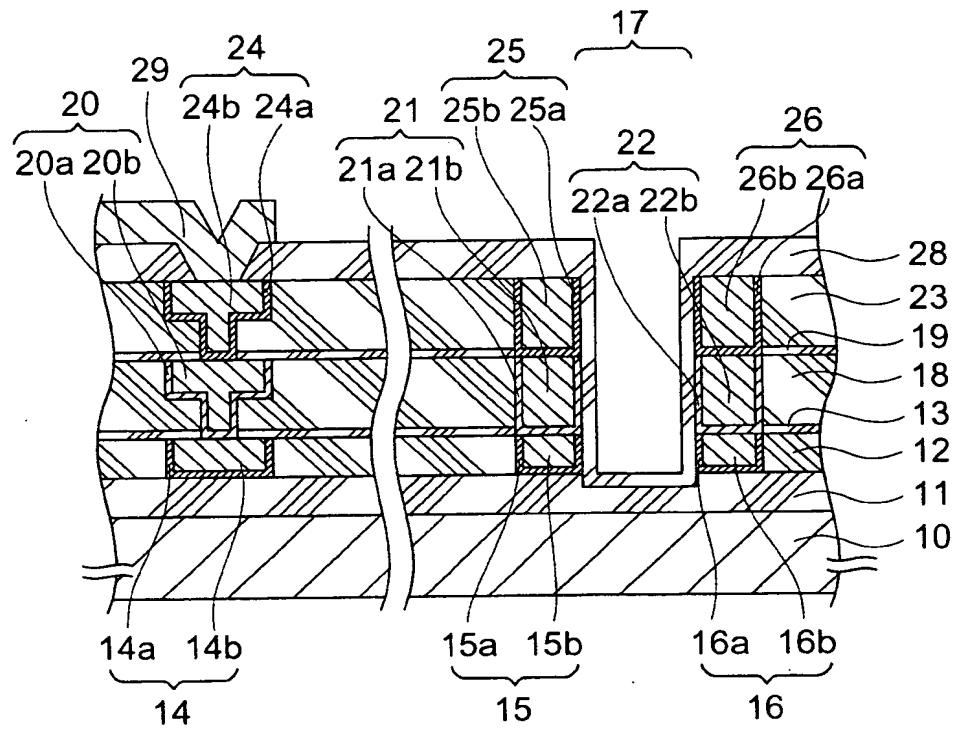


FIG. 3B

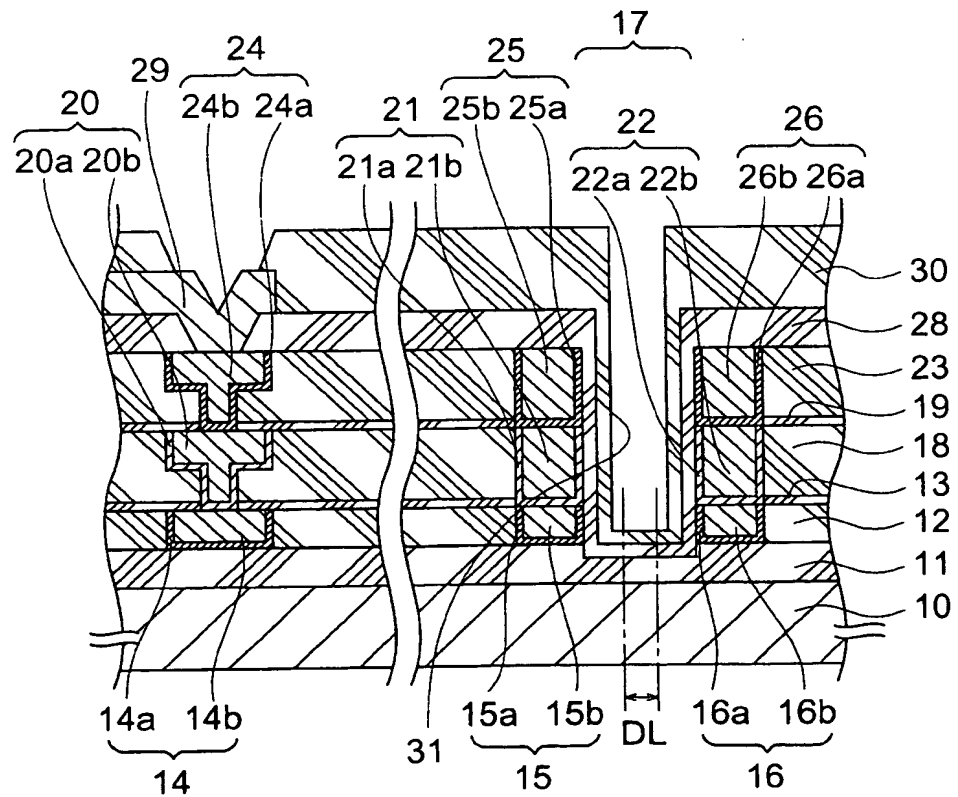


FIG. 4

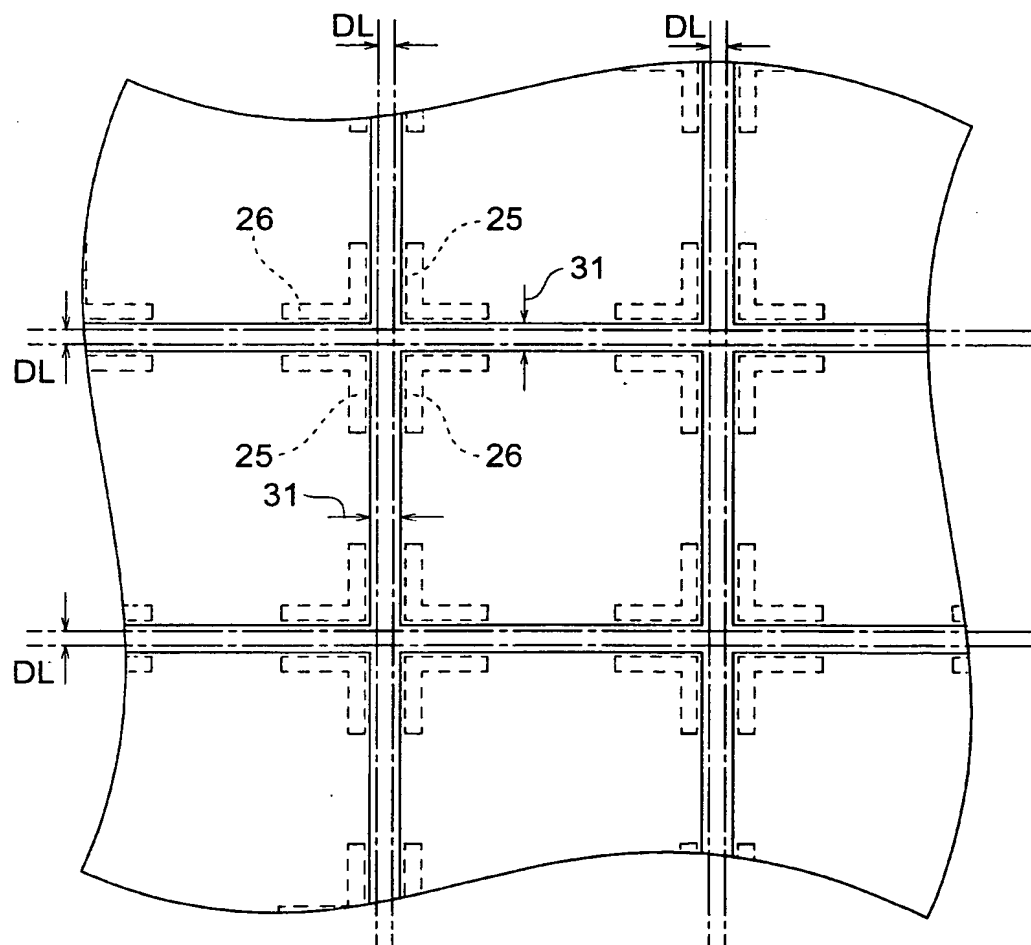
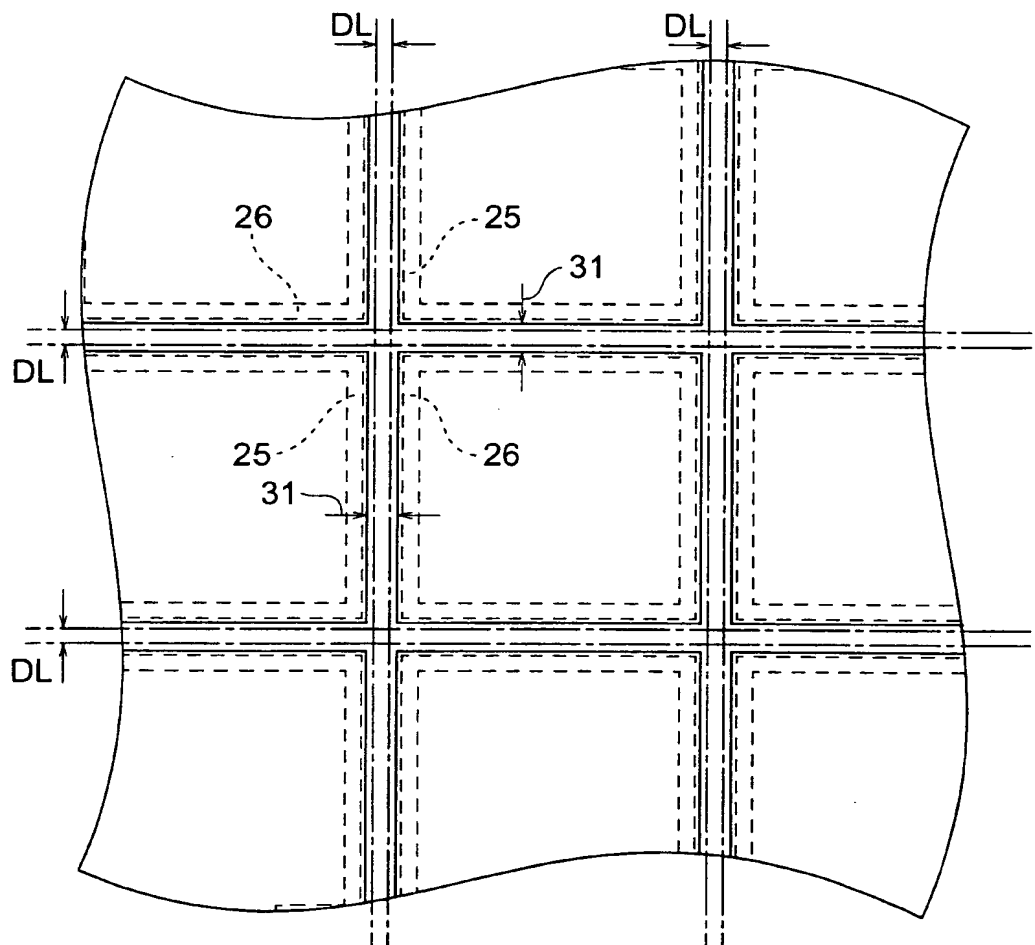


FIG. 5



[illegible]

A cross-sectional view of a semiconductor device. The device consists of a substrate 10 with multiple layers 11, 12, 13, 18, 19, 23, and 27. A patterned structure 14 is formed on the substrate, with regions 14a and 14b. A vertical line 17 is shown. The patterned structure 14 is composed of regions 20a and 20b, and regions 24a and 24b. The regions 20a and 20b are connected by a vertical line 17. The regions 24a and 24b are connected by a vertical line 17. The regions 20a and 20b are connected by a vertical line 17. The regions 24a and 24b are connected by a vertical line 17.

FIG. 8

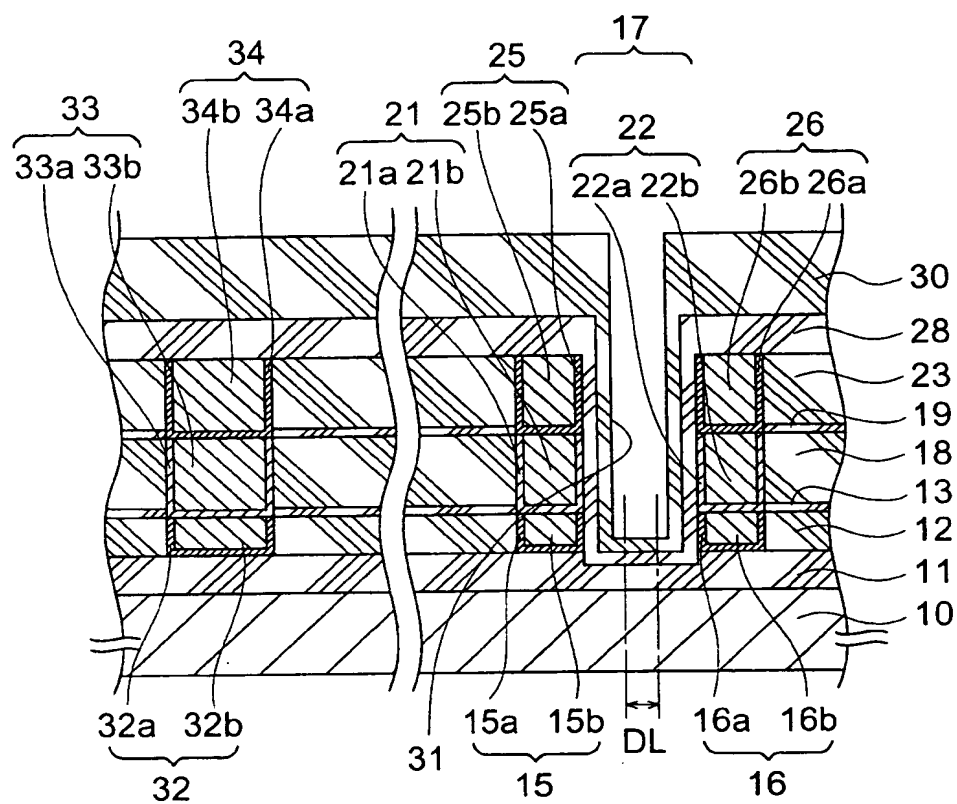


FIG. 9

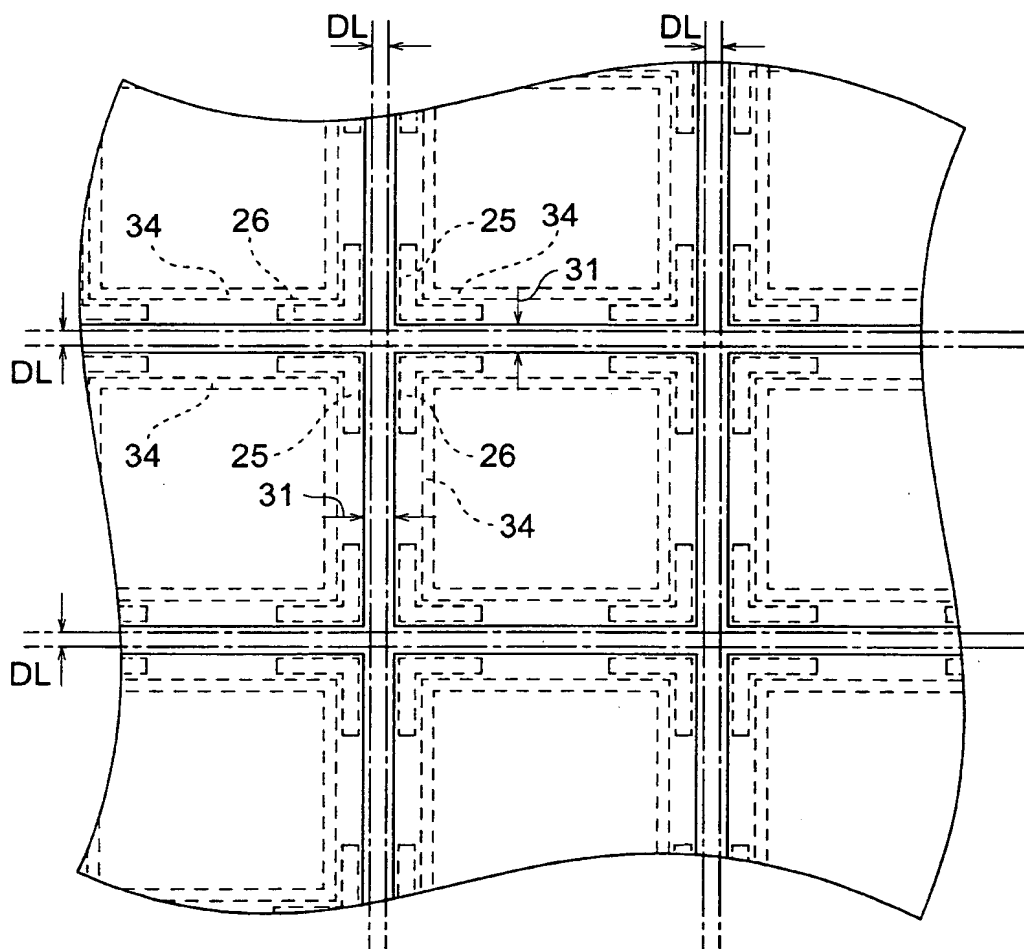


FIG. 10A

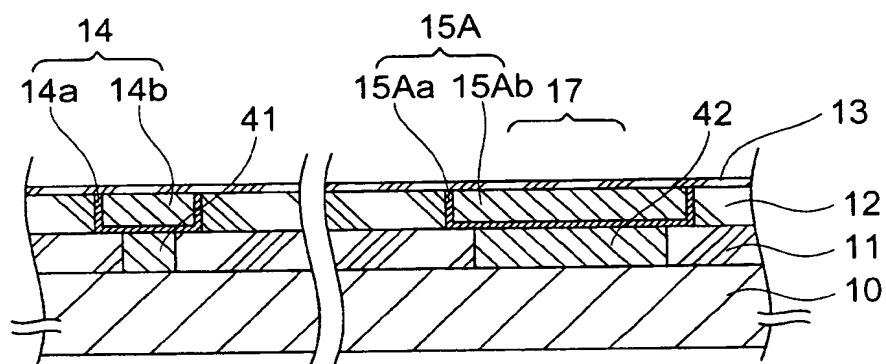


FIG. 10B

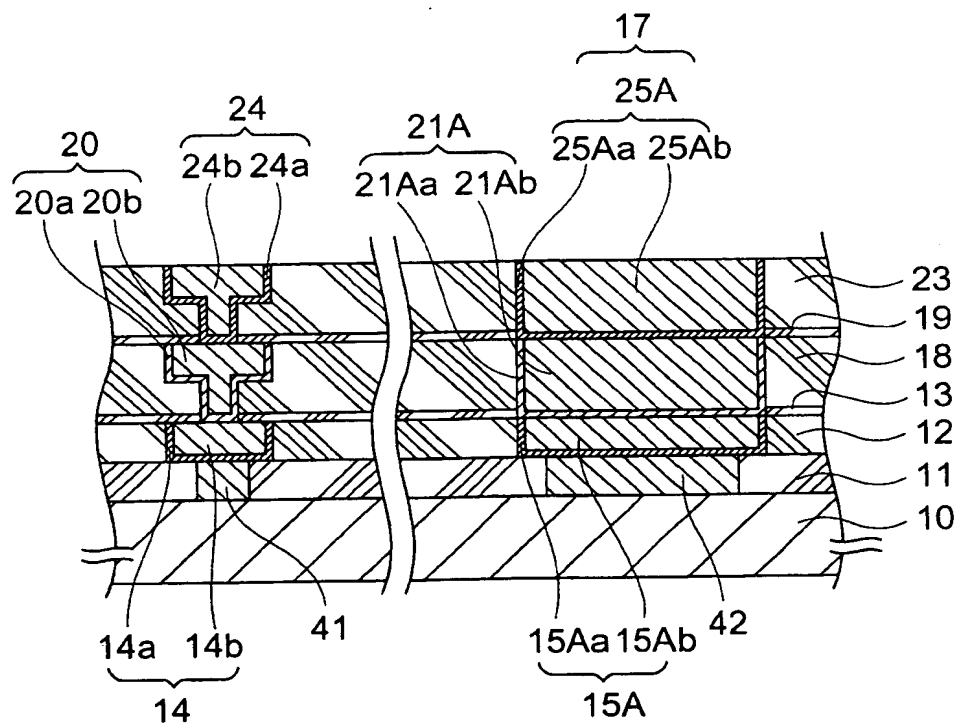


FIG. 11A

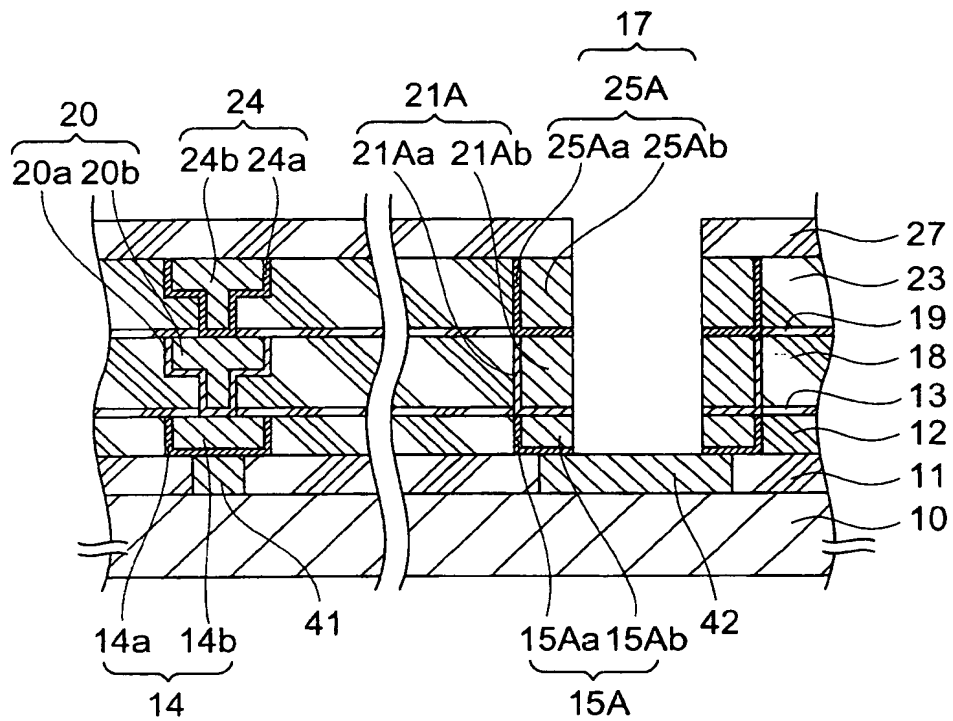


FIG. 11B

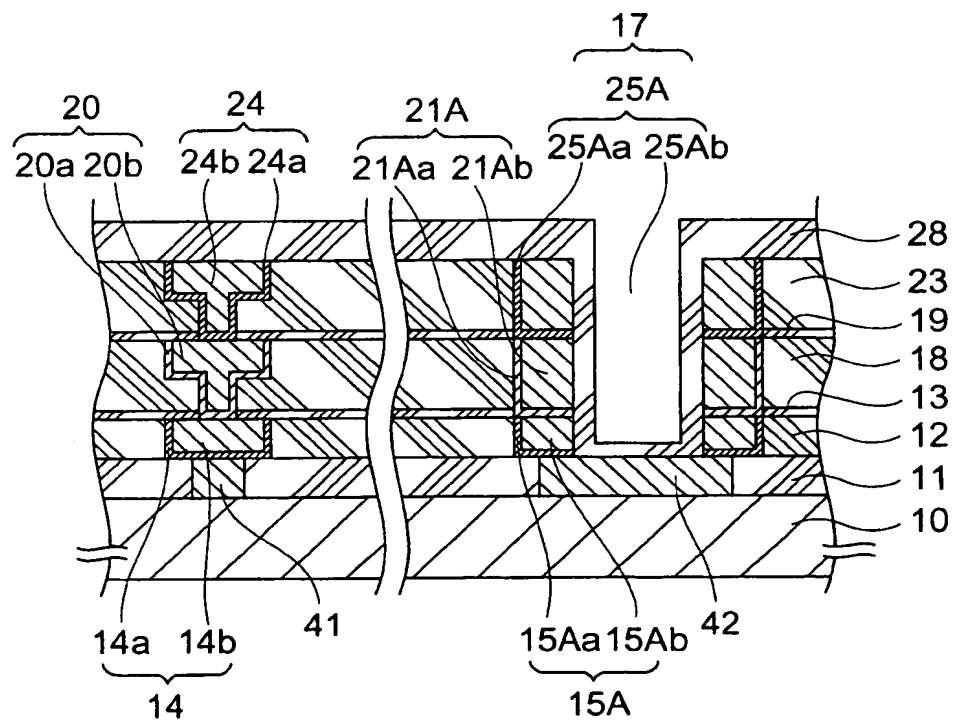


FIG. 12A

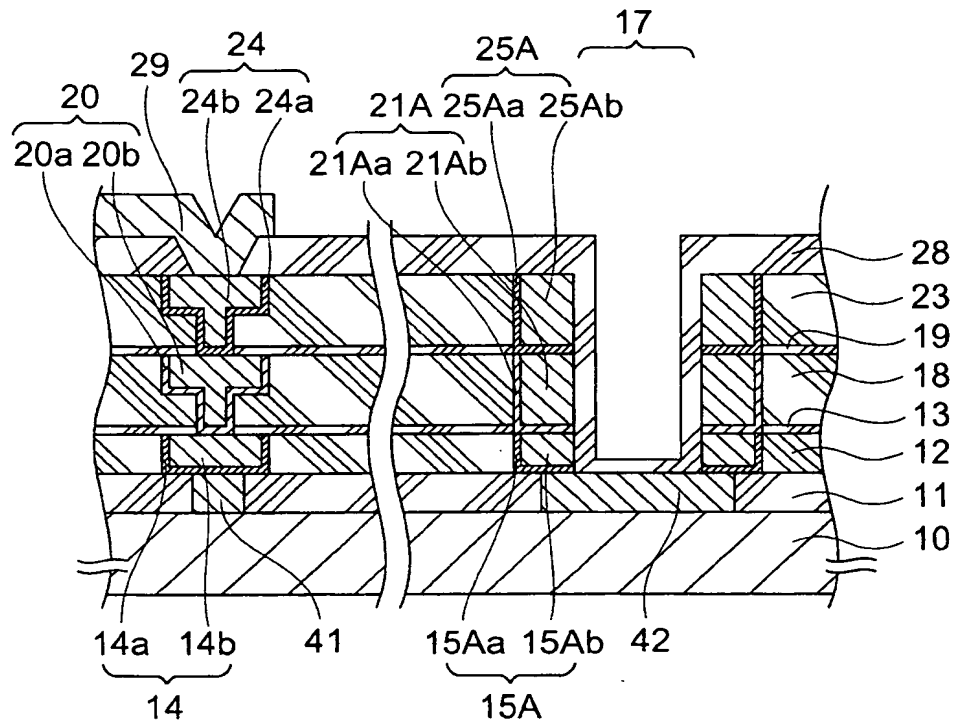


FIG. 12B

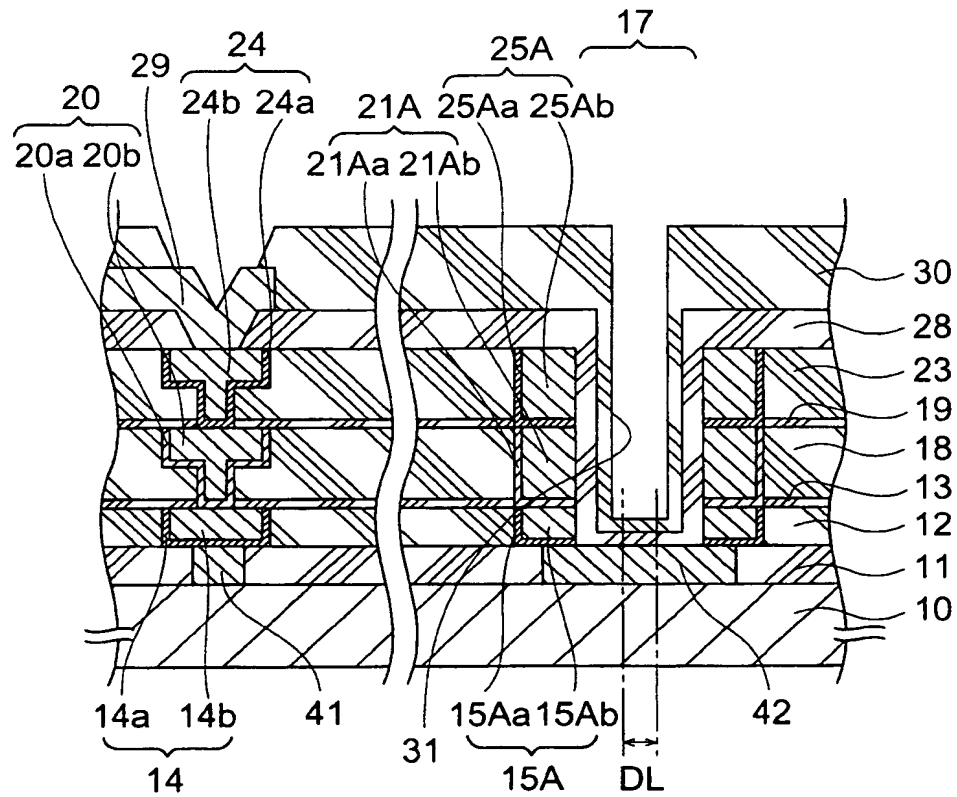


FIG. 13

